## VS-ST1280C..K Series

**Vishay Semiconductors** 



### **Phase Control Thyristors** (Hockey-PUK Version), 2310 A



A-24 (K-PUK)

#### **PRODUCT SUMMARY** Package A-24 (K-PUK) Diode variation Single SCR 2310 A I<sub>T(AV)</sub> 400 V, 600 V V<sub>DRM</sub>/V<sub>RRM</sub> V<sub>TM</sub> 1.44 V $I_{GT}$ 100 mA -40 °C to 125 °C ТJ

### **FEATURES**

- · Center amplifying gate
- · Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- · Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		2310	А			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
		4150	A			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
1	50 Hz	42 500	٨			
I <sub>TSM</sub>	60 Hz	44 500	— A			
124	50 Hz	9027	kA <sup>2</sup> s			
l <sup>2</sup> t	60 Hz	8240	KA <sup>2</sup> S			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V			
t <sub>q</sub>	Typical	200	μs			
TJ		-40 to 125	°C			

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM/</sub> V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$				
VS-ST1280CK	04	400	500	100				
V3-3112000K	06	600	700	100				

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COMPLIANT

# VS-ST1280C..K Series



Vishay Semiconductors

ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	m average on-state current 180° conduction, half sine wave		180° conduction, half sine wave 2310		2310 (885)	А
at heatsink temperature	I <sub>T(AV)</sub>	Double side (single side) cooled		55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	25 °C heats	ink temperature	e double side cooled	4150	
		t = 10 ms	No voltage		42 500	
Maximum peak, one-cycle	I <sub>TSM</sub>	t = 8.3 ms	reapplied		44 500	A kA <sup>2</sup> s
non-repetitive surge current		t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	35 700	
		t = 8.3 ms	reapplied		37 400	
	l <sup>2</sup> t	t = 10 ms	No voltage reapplied 100 % V <sub>RRM</sub>		9027	
Maximum I <sup>2</sup> t for fusing		t = 8.3 ms			8241	
	1-1	t = 10 ms			6383	
		t = 8.3 ms	reapplied		5828	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	e reapplied	90 270	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.83	v
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), T <sub>J</sub> = T <sub>J</sub> maxin	0.90	v	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), T <sub>J</sub> = T <sub>J</sub> maximum			0.077	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J$ maximum			0.068	11152
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk} = 8000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$		num, t <sub>p</sub> = 10 ms sine pulse	1.44	V
Maximum holding current	Ι <sub>Η</sub>	$T_{ij} = 25 \text{ °C}$ , anode supply 12 V resistive load		600	mA	
Typical latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1		1000	IIIA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,  t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.9	
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	200	μs

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNIT S				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs				
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA				

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TRIGGERING								
PABAMETER	SYMBOL	ТЕ	VALUES		UNITS			
	STNIDOL	15	ST CONDITIONS	typ.	max.	UNITS		
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤5 ms	1	6	w		
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	:	3	vv		
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	А		
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms		maximum, t <sub>p</sub> ≤ 5 ms		20	v
Maximum peak negative gate voltage	- V <sub>GM</sub>		5.0		v			
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	mA		
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200			
		T <sub>J</sub> = 125 °C		50	-			
		T <sub>J</sub> = -40 °C		1.4	-			
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V		
		T <sub>J</sub> = 125 °C	1		-			
DC gate current not to trigger	I <sub>GD</sub>	T. T. maximum	Maximum gate current/voltage not to trigger is the maximum	10		mA		
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.	25	v		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS		
Maximum operating temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal resistance, junction to	Б	DC operation single side cooled	0.042			
heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W		
Maximum thermal resistance, access to be stainly	D	DC operation single side cooled	0.006			
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	A-24 (K-	PUK)		

$\Delta \mathbf{R}_{thJC}$ CONDUCTION										
SINUSOIDAL CONDUCTION			RECTANGULAR	R CONDUCTION	TEST CONDITIONS	UNITS				
CONDUCTION ANGLE	SINGLE SIDE DOUBLE SIDE				SINGLE SIDE DOUBLE SIDE		LE SIDE SINGLE SIDE DOUBLE SIDE		TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002						
120°	0.004	0.004	0.004	0.004						
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W				
60°	0.007	0.007	0.007	0.007						
30°	0.012	0.012	0.012	0.012						

Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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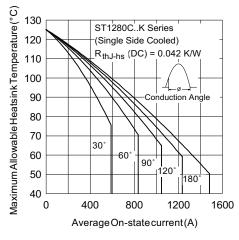


Fig. 1 - Current Ratings Characteristics

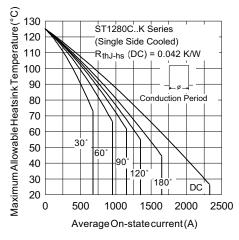


Fig. 2 - Current Ratings Characteristics

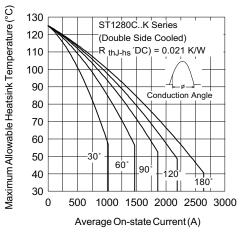


Fig. 3 - Current Ratings Characteristics

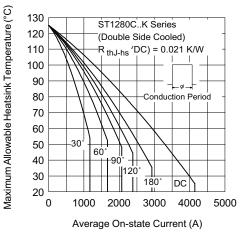


Fig. 4 - Current Ratings Characteristics

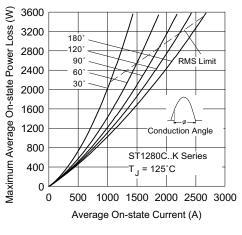


Fig. 5 - On-State Power Loss Characteristics

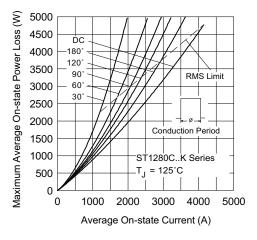


Fig. 6 - On-State Power Loss Characteristics

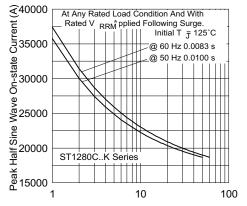
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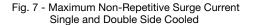
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Number Of Equal Amplitude Half Cycle Current Pulses (N)



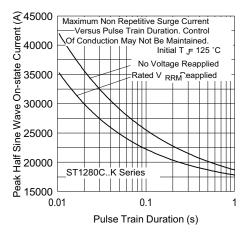


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

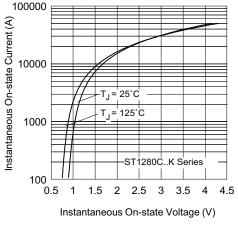
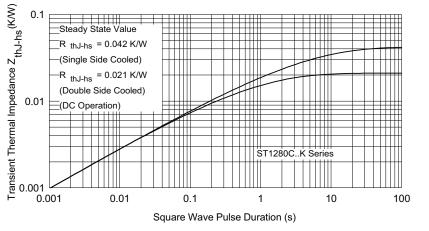


Fig. 9 - On-State Voltage Drop Characteristics





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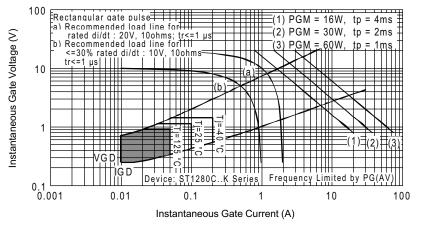


Fig. 11 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

www.vishay.com

Device code	VS-	ST	128	0	с	06	к	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -	Visł	nay Sem	niconduc	ctors pro	oduct				
	2 -	Thy	ristor							
	3 -	Ess	ential pa	art numł	ber					
	4 -	0 =	Conver	ter grade	e					
	5 -	C =	Cerami	c PUK						
	6 -	Volt	tage coo	le x 100	= V <sub>RRM</sub>	<sub>I</sub> (see V	oltage I	Ratings	table)	
	7 -	K =	PUK ca	ise A-24	(K-PUł	<)				
	8 -	0 =	Eyelet t	erminals	s (gate a	and aux	iliary ca	thode u	Insolder	ed leads
		1 =	Fast-on	termina	als (gate	and au	xiliary c	athode	unsolde	ered lead
		2 =	Eyelet t	erminals	s (gate a	and aux	iliary ca	thode s	oldered	leads)
		3 =	Fast-on	termina	als (gate	and au	xiliary c	athode	soldere	d leads)
	9 -	Crit	ical dV/o	dt: • Noi	ne = 50	0 V/µs (	standar	d select	tion)	
				• L =	1000 V	/µs (spe	ecial sel	ection)		

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95081				

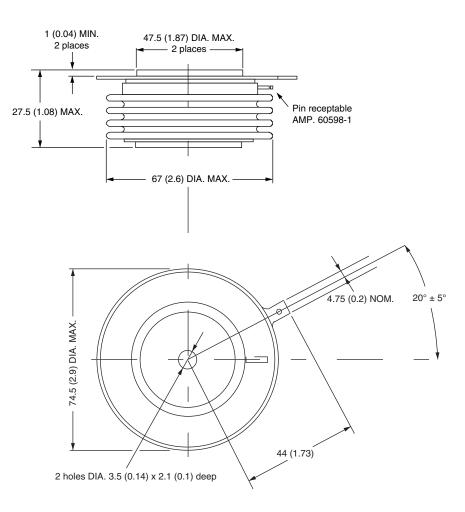
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## A-24 (K-PUK)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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